

Technical Data
Data Sheet N1166, Rev. -

**Green Products** 

# 126NQ200-1 SCHOTTKY RECTIFIER

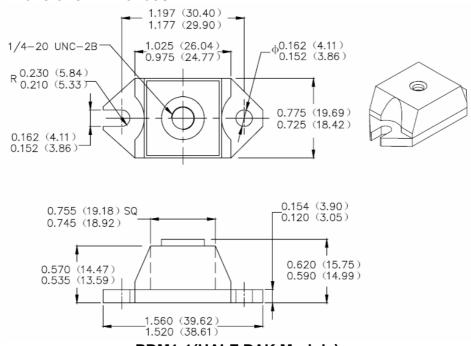
#### **Applications:**

• Switching power supply • Converters • Free-Wheeling diodes • Reverse battery protection

#### Features:

- 175°C T<sub>J</sub> operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5'S
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Mechanical Dimensions: In Inches / mm**



# PRM1-1(HALF PAK Module)

#### MARKING, MOLDING RESIN

Marking for 126NQ200-1, 1<sup>st</sup> row SS YYWWL, 2<sup>nd</sup> row 126NQ200-1 Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number Molding resin

Epoxy resin UL:94V-0



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## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	200	V
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>C</sub> =110℃, rectangular wave form	120	А
Peak One Cycle Non- Repetitive Surge Current (per leg)	I <sub>FSM</sub>	8.3 ms, half Sine pulse	2500	А

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 120A, Pulse, T <sub>J</sub> = 25 °C	1.12	V
	$V_{F2}$	@ 120A, Pulse, T <sub>J</sub> = 125 °C	0.79	V
Reverse Current (per leg) *	I <sub>R1</sub>	$@V_R = \text{rated } V_R T_J = 25  ^{\circ}\text{C}$	3	mA
	$I_{R2}$	$@V_R = \text{rated } V_R T_J = 125  ^{\circ}\text{C}$	45	mΑ
Junction Capacitance (per leg)	C <sub>T</sub>	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	1800	pF
Typical Series Inductance (per leg)	L <sub>S</sub>	Measured lead to lead 5 mm from package body	6.0	nH
Voltage Rate of Change	dv/dt	-	10,000	V/μs

Pulse Width < 300µs, Duty Cycle <2%

# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specific	Units		
Max. Junction Temperature	TJ	-	-55 to +175		°C	
Max. Storage Temperature	T <sub>stg</sub>	-	-55 to +175		°C	
Maximum Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.40		°C/W	
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.15		°C/W	
Mounting Torque	Тм	Non-lubricated threads	Mounting Torque Terminal Torque	23(min) 29(max) 35(min) 46(max)	Kg-cm	
Approximate Weight	wt	-	25.6		g	
Case Style	PRM1-1					

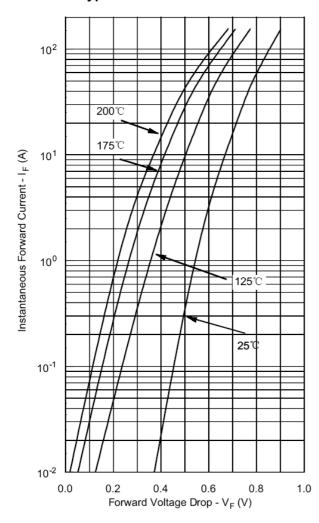
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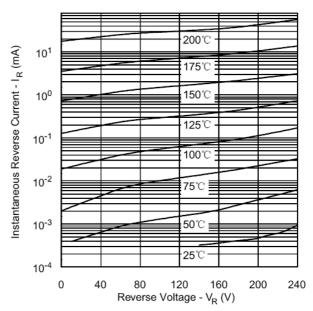


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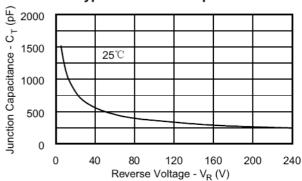
### **Typical Forward Characteristics**



# **Typical Reverse Characteristics**



# Typical Junction Capacitance



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